

	Type	L #	Hits	Search Text	DBs	Time Stamp
1	BRS	L1	2299	359/224,290-292,295,298,350,847.cc1s.	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 14:58 ; IBM_TDB	
2	BRS	L2	55199	electro-optic\$ or electrooptic\$	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 14:58 ; IBM_TDB	
3	BRS	L3	703098	silicon	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 14:58 ; IBM_TDB	
4	BRS	L4	1214717	semiconductor\$2 or semi-conductor\$2	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:00 ; IBM_TDB	
5	BRS	L5	9592	2 and 3	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:00 ; IBM_TDB	

Type	L #	Hits	Search Text	DBs	Time Stamp
6	BRS L6 121	1 and 5		USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:01 ; IBM_TDB	
7	BRS L7 357624	membrane\$2		USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:01 ; IBM_TDB	
8	BRS L8 638	5 and 7		USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:01 ; IBM_TDB	
9	BRS L9 41	1 and 8		USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:05 ; IBM_TDB	
10	BRS L10 318125	mars or ((anti-reflect44 or antireflect\$4) near3 switch\$4)		USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:08 ; IBM_TDB	

	Type	L #	Hits	Search Text	DBs	Time Stamp
11	BRS	L1 1	2178	1 not 6	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:08 ;	
12	BRS	L1 2	248	2 and 3 and 7 and 10	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:08 ;	
13	BRS	L1 3	234	12 not 9	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:19 ;	
14	BRS	L1 4	2	goosen-keith\$.in.	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:20 ;	
15	BRS	L1 5	3	goosen-k\$.in.	USPAT; US-PGPU B; EPO; 2003/ JPO; 03/20 DERWENT 15:20 ;	

Type	L #	Hits	Search Text	DBs	Time Stamp
16	BRS	L1 6	104 goossen-keith\$ .in.	USPAT; US-PGPU; B; EPC; 2003/ JPO; 03/20 DERWENT; 15:20 ; IBM_TDB	
17	BRS	L1 7	15 10 and 16	USPAT; US-PGPU; B; EPO; 2003/ JPO; 03/20 DERWENT; 15:20 ; IBM_TDB	

Document ID	S o u r c e	Issu e Date	Pa ge s	Title	Current OR	Current XRef
1	U S -					
1	US 20020109904 A1	P 2002 G 0815	13	Fast attenuator	359/291	359/290; 359/292
2	U S -					
2	US 4203128 A	P 1980 A 0513	11	Electrostatically deformable thin silicon membranes	331/156	257/E19; .324; 361/291; ;
3	U S -					
3	US 5231532 A	P 1993 A 0727	8	Switchable resonant filter for optical radiation	359/295	359/578; 359/586; 359/589
4	U S -					
4	US 5506919 A	P 1996 A 0409	12	Conductive membrane optical modulator	385/1	385/2; 385/23
5	U S -					
5	US 5510277 A	P 1996 A 0423	11	Surface treatment for silicon substrates	438/707	134/1.3; 438/974
6	U S -					
6	US 5943155 A	P 1999 A 0824	13	Mars optical modulators	359/247	359/290; 359/291; 359/295; 359/318

Document ID	Issue Date	Page(s)	Title	Current OR	Current XRef
7 US 5943155 A	1999 08/24	D E F W E N T U S P A T	Double poly mechanical antireflection switch (MARS) device for optical modulators	359/290 ; 359/295 ; 359/318	359/223 ; 359/224 ; 359/220 ; 359/291 ; 359/318 ; 359/318
8 US 5943156 A	1999 08/24	U S P A T	Micro-mechanical, anti-reflection, switched optical modulator array and fabrication method	359/291 ; 359/295 ; 359/318	359/223 ; 359/224 ; 359/220 ; 359/291 ; 359/318 ; 359/318
9 US 5949571 A	1999 09/07	U S P A T	Mars optical modulators	359/291 ; 359/295 ; 359/318 ; 439/321	359/223 ; 359/224 ; 359/220 ; 359/291 ; 359/295 ; 359/318 ; 359/318 ; 439/321
10 US 6337753 B1	2002 01/08	U S P A T	Optical power equalizer	359/124 ; 359/291	359/190 ; 359/124 ; 359/291
11 US 6462858 B1	2002 10/08	U S P A T	Fast attenuator	359/290 ; 359/295 ; 359/347	359/237 ; 359/191 ; 359/195 ; 359/347
12 US 6519073 B1	2003 02/11	U S P A T	Micromechanical modulator and methods for fabricating the same	359/290 ; 359/291	359/248 ; 359/291